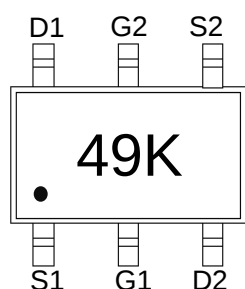


Features

- Surface Mount Package
- Low $R_{DS(on)}$
- Operated at Low Logic Level Gate Drive
- ESD Protected Gate

Application

- Load/ Power Switching
- Interfacing Switching
- Battery Management for Ultra Small Portable Electronics
- Logic Level Shift

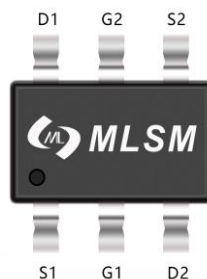


49K: Device code

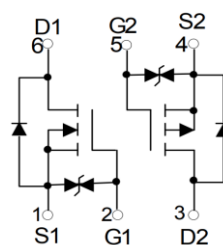
Marking and pin assignment

Product Summary

V_{DS}	$R_{DS(on)}$ TYP	I_D
20V	100mΩ@4.5V	0.75A
	135mΩ@2.5V	
-20V	380mΩ@-4.5V	-0.66A
	520mΩ@-2.5V	



SOT-363 top view



Schematic diagram



Halogen-Free

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	N-Channel	P-Channel	Unit
V_{DS}	Drain-Source Breakdown Voltage	20	-20	V
V_{GS}	Gate-Source Voltage	±12	±12	V
T_J	Maximum Junction Temperature	150	150	°C
T_{STG}	Storage Temperature Range	-55 to 150	-55 to 150	°C
I_S	Diode Continuous Forward Current	$T_c=25^{\circ}\text{C}$		A
		0.75	-0.66	

Mounted on Large Heat Sink

I_{DM}	Pulse Drain Current Tested	$T_c=25^{\circ}\text{C}$	1.8	-1.2	A
I_D	Continuous Drain Current	$T_c=25^{\circ}\text{C}$	0.75	-0.66	A
$R_{\theta JA}$	Thermal Resistance Junction-Ambient		883	883	°C/W
E_{SD}	Gate-Source ESD Rating (HBM, Method 3015)		2000	-2000	V

Ordering Information (Example)

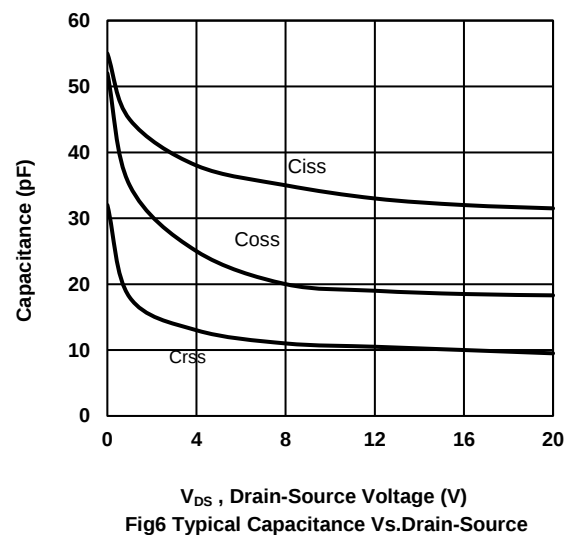
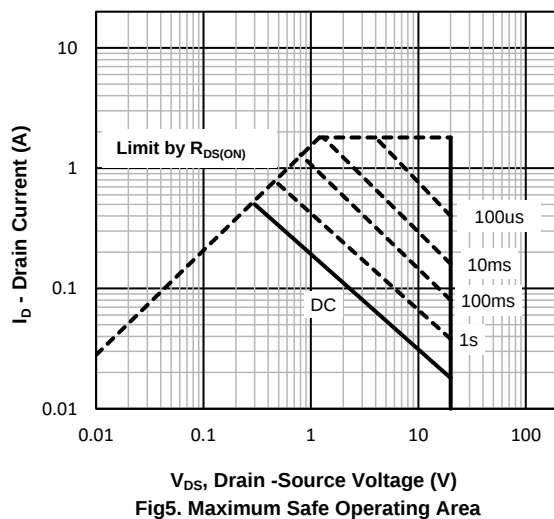
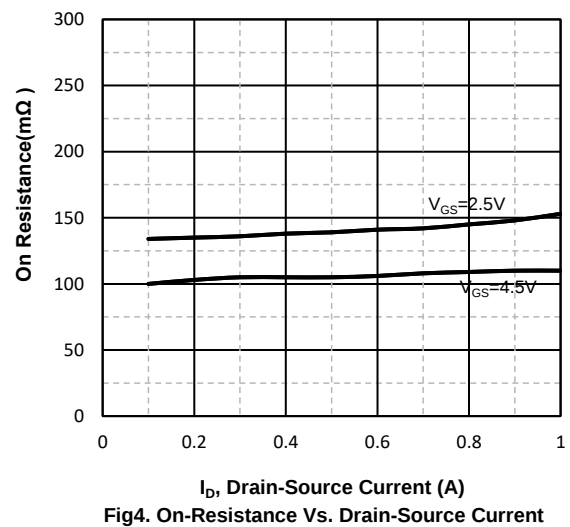
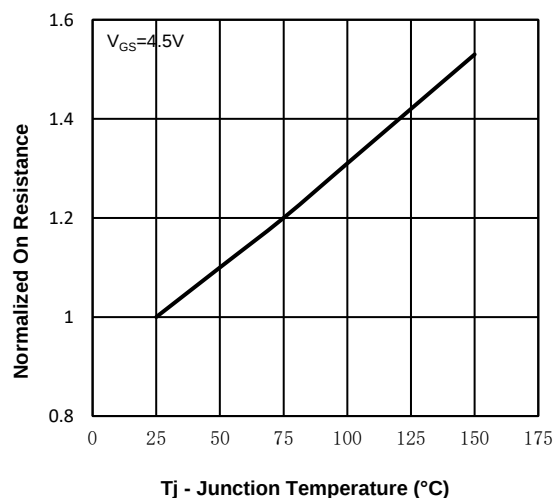
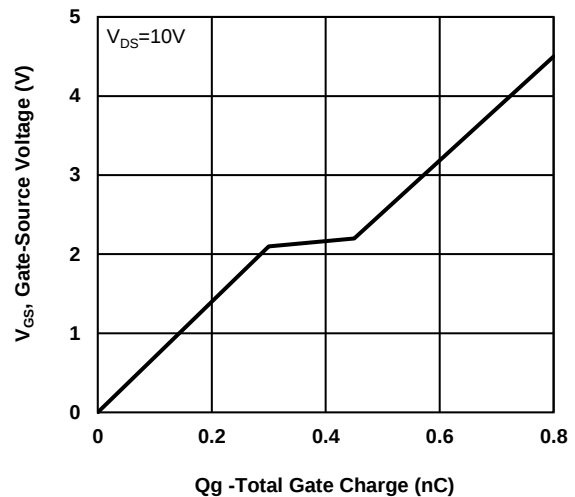
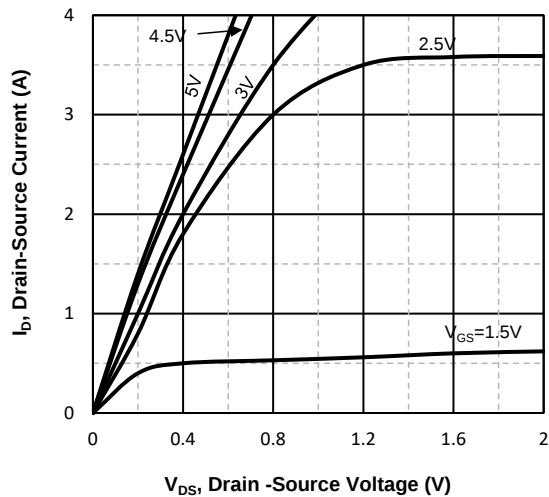
Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
MLS3439KDW	SOT-363	49K	3,000	45,000	180,000	7"reel

N-Ch Electrical Characteristics (TJ=25℃ unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ TJ = 25℃ (unless otherwise stated)						
BV _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _b =250μA	20	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =20V, V _{GS} =0V	--	--	1.0	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±10V, V _{DS} =0V	--	--	±20	μA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _b =250μA	0.35	0.7	1.1	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =4.5V, I _b =0.65A	--	100	380	mΩ
		V _{GS} =2.5V, I _b =0.55A	--	135	450	mΩ
		V _{GS} =1.8V, I _b =0.45A	--	200	800	mΩ
Dynamic Electrical Characteristics @ TJ = 25℃ (unless otherwise stated)						
C _{ISS}	Input Capacitance	V _{DS} =10V, V _{GS} =0V, f=1MHz	--	33	--	pF
C _{OSS}	Output Capacitance		--	21	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	10	--	pF
Switching Characteristics						
Q _g	Total Gate Charge	V _{DS} =10V, I _b =0.75A, V _{GS} =4.5V	--	0.8	--	nC
Q _{gs}	Gate Source Charge		--	0.3	--	nC
Q _{gd}	Gate Drain Charge		--	0.17	--	nC
t _{d(on)}	Turn-on Delay Time	V _{DD} =10V, I _b =0.75A, V _{GS} =4.5V, R _G =10Ω	--	4.2	--	nS
t _r	Turn-on Rise Time		--	19.1	--	nS
t _{d(off)}	Turn-Off Delay Time		--	10.3	--	nS
t _f	Turn-Off Fall Time		--	24	--	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	Tj=25℃, Is=0.75A	--	--	1.2	V

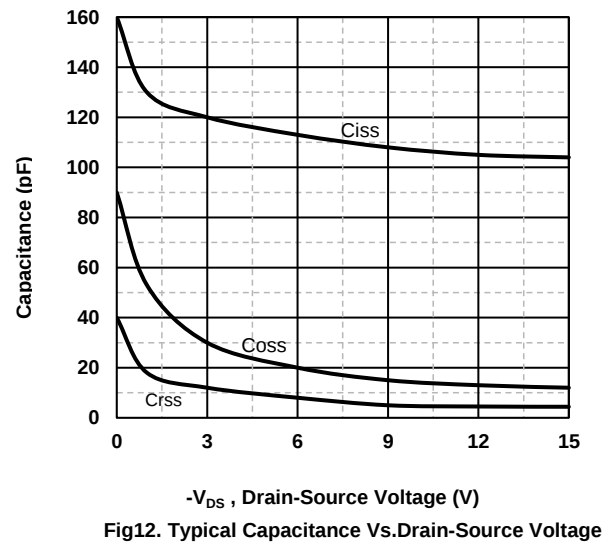
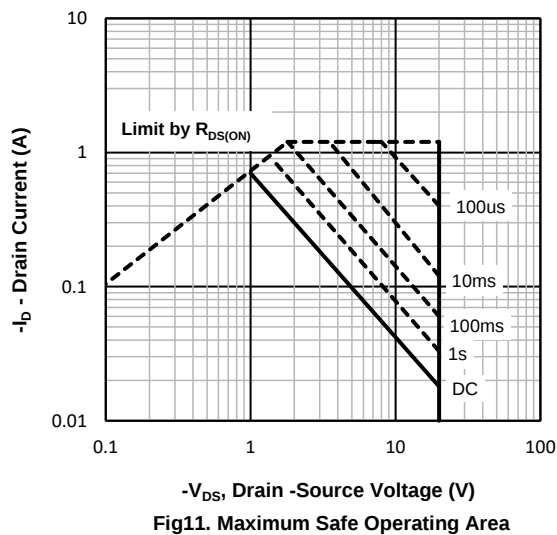
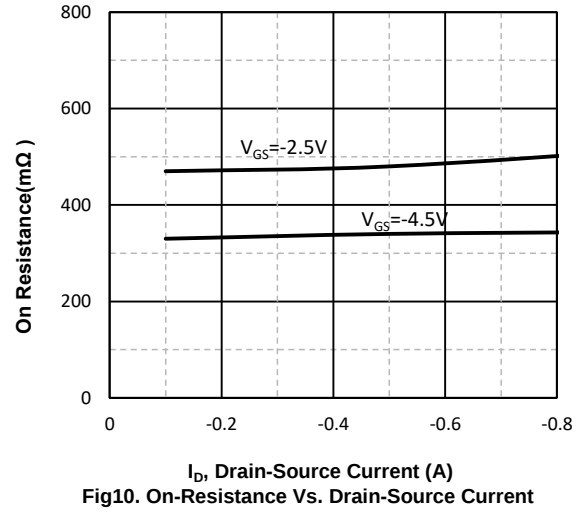
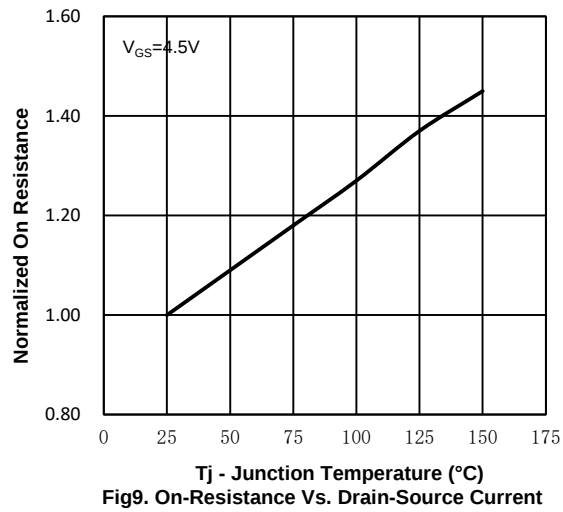
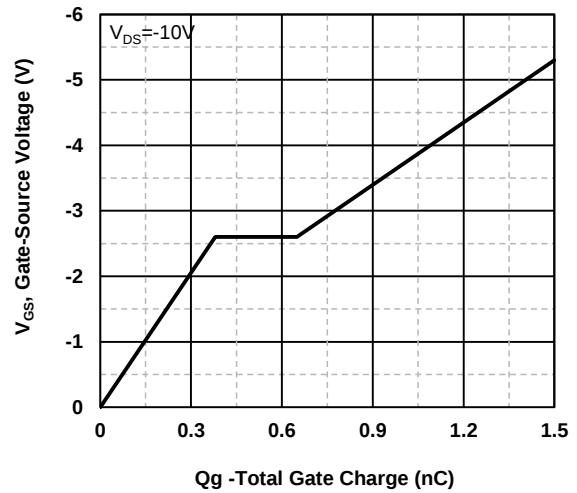
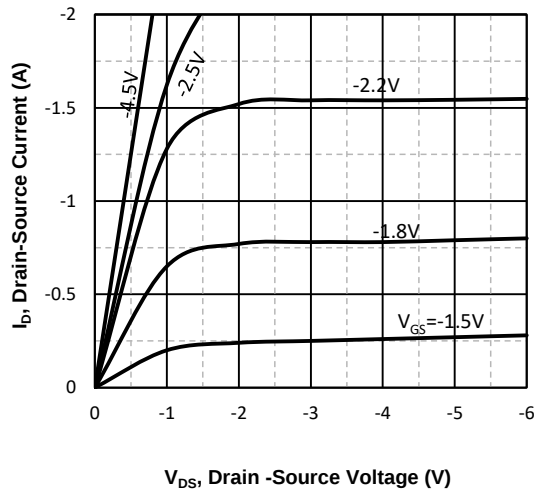


P-Ch Electrical Characteristics (TJ=25℃ unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ TJ = 25℃ (unless otherwise stated)						
BV _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250μA	-20	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-20V, V _{GS} =0V	--	--	-1.0	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±10V, V _{DS} =0V	--	--	±20	μA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-0.35	-0.65	-1.1	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =-4.5V, I _D =-1.0A	--	380	520	mΩ
		V _{GS} =-2.5V, I _D =-0.8A	--	520	700	mΩ
		V _{GS} =-1.8V, I _D =-0.5A	--	750	--	mΩ
Dynamic Electrical Characteristics @ TJ = 25℃ (unless otherwise stated)						
C _{ISS}	Input Capacitance	V _{DS} =-10V, V _{GS} =0V, f=1MHz	--	115	--	pF
C _{OSS}	Output Capacitance		--	15	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	8.8	--	pF
Switching Characteristics						
Q _g	Total Gate Charge	V _{DD} =-10V, I _D =-0.66A, V _{GS} =-4.5V	--	1.25	--	nC
Q _{gs}	Gate Source Charge		--	0.35	--	nC
Q _{gd}	Gate Drain Charge		--	0.29	--	nC
t _{d(on)}	Turn-on Delay Time	V _{DS} =-10V, I _D =-0.66A, V _{GS} =-4.5V, R _G =10Ω	--	9	--	nS
t _r	Turn-on Rise Time		--	5.5	--	nS
t _{d(off)}	Turn-Off Delay Time		--	30.8	--	nS
t _f	Turn-Off Fall Time		--	20	--	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	Tj=25℃, Is=-0.66A	--	--	-1.2	V

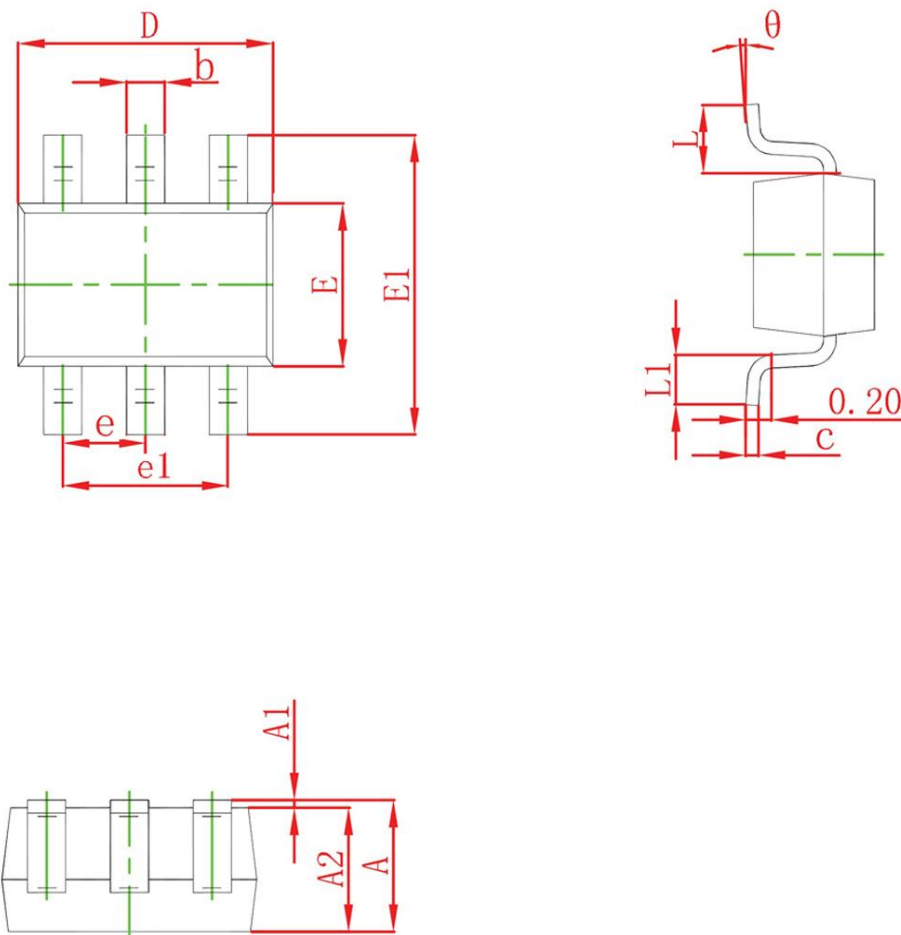
N-Ch Typical Operating Characteristics



P-Ch Typical Operating Characteristics



SOT-363 Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.150	0.350	0.006	0.014
c	0.100	0.150	0.004	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.400	0.085	0.094
e	0.650TYP		0.026TYP	
e1	1.200	1.400	0.047	0.055
L	0.525REF		0.021REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°